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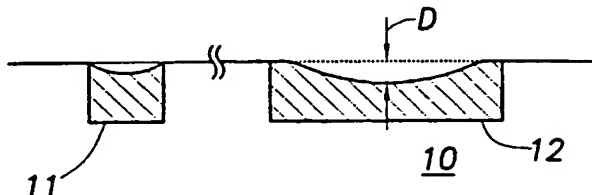
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(54) Title: ABRASIVE-FREE METAL CMP IN PASSIVATION DOMAIN



(57) Abstract: Metal CMP with reduced dishing and overpolish insensitivity is achieved with an abrasive-free polishing composition having a pH and oxidation-reduction potential in the domain of passivation of the metal and, therefore, a low static etching rate at high temperatures, e.g., higher than 50°. Embodiments of the present invention comprise CMP of Cu film without any abrasive using a composition comprising one or more chelating agents, one or more

oxidizers, one or more corrosion inhibitors, one or more agents to achieve a pH of about 3 to about 10 and deionized water.

ABRASIVE-FREE METAL CMP IN PASSIVATION
DOMAIN

Technical Field

The present invention relates generally to metal polishing and, particularly, to planarizing copper (Cu) and/or Cu alloy metallization in manufacturing semiconductor devices with reduced dishing and overpolish insensitivity. The present invention is applicable to manufacturing high speed integrated circuits having submicron design features and high conductivity interconnect structures with improved reliability.

Background Art

The escalating requirements for high density and performance associated with ultra large scale integration semiconductor wiring require responsive changes in interconnection technology. Such escalating requirements have been found difficult to satisfy in terms of providing a low RC (resistance and capacitance) interconnect pattern, particularly wherein submicron vias, contacts and conductive lines have high aspect ratios imposed by miniaturization.

Conventional semiconductor devices comprise a semiconductor substrate, typically doped monocrystalline silicon, and a plurality of sequentially formed interlayer dielectrics and conductive patterns. An integrated circuit is formed containing a plurality of conductive patterns comprising conductive lines separated by interwiring spacings, and a plurality of interconnect lines, such as bus lines, bit lines, word lines and logic interconnect lines. Typically, the conductive patterns on different layers, i.e., upper and lower layers, are electrically connected by a conductive plug filling a via hole, while a conductive plug filling a contact hole establishes electrical contact with an action region on a semiconductor substrate, such as a source/drain region. Conductive lines are formed in trenches which typically extend substantially horizontal with respect to the semiconductor substrate. Semiconductor "chips" comprising five or more levels of metallization are becoming more prevalent as device geometries shrink to submicron levels.

A conductive plug filling a via hole is typically formed by depositing an interlayer dielectric on a conductive layer comprising at least one conductive pattern, forming an

opening through the interlayer dielectric by conventional photolithographic and etching techniques, and filling the opening with a conductive material, such as tungsten (W). Excess conductive material on the surface of the dielectric interlayer is typically removed by chemical mechanical polishing (CMP). One such method is known as damascene and
5 basically involves forming an opening in the dielectric interlayer and filling the opening with a metal. Dual damascene techniques involve forming an opening comprising a lower contact or via hole section in communication with an upper trench section. The entire opening is filled with a conductive material, typically a metal, to simultaneously form a conductive plug in electrical contact with a conductive line.

10 Cu and Cu alloys have received considerable attention as a candidate for replacing Al in interconnect metallizations. Cu is relatively inexpensive, easy to process, and has a lower resistivity than Al. In addition, Cu has improved electrical properties vis-à-vis W, making Cu a desirable metal for use as a conductive plug as well as conductive wiring.

An approach to forming Cu plugs and wiring comprises the use of damascene
15 structures employing CMP. However, due to Cu diffusion through interdielectric layer materials, such as silicon dioxide, Cu interconnect structures must be encapsulated by a diffusion barrier layer. Typical diffusion barrier metals include tantalum (Ta), tantalum nitride (Ta₃N₅), titanium nitride (TiN), titanium-tungsten (TiW), tungsten (W), tungsten nitride (WN), titanium-titanium nitride (Ti-TiN), titanium silicon nitride (TiSiN), tungsten
20 silicon nitride (WSiN), tantalum silicon nitride (TaSiN) and silicon nitride for encapsulating Cu. The use of such barrier metals to encapsulate Cu is not limited to the interface between Cu and the dielectric interlayer, but includes interfaces with other metals as well.

In conventional CMP techniques, a wafer carrier assembly is in contact with a polishing pad in a CMP apparatus. The wafers are typically mounted on a carrier or
25 polishing head which provides a controllable pressure urging the wafers against the polishing pad. The pad has a relative movement with respect to the wafer driven by an external driving force. Thus, the CMP apparatus effects polishing or rubbing movement between the surface of each thin semiconductor wafer and the polishing pad while dispersing a polishing slurry containing abrasive particles in a reactive solution to effect
30 both chemical activity and mechanical activity while applying a force between the wafer and a polishing pad. A different type of abrasive article from the above-mentioned abrasive slurry-type polishing pad is fixed abrasive article, e.g., fixed abrasive polishing pad. Such a

fixed abrasive article typically comprises a backing sheet with a plurality of geometric abrasive composite elements adhered thereto.

It is extremely difficult to planarize a metal surface, particularly a Cu surface, as by CMP of a damascene inlay, with a high degree of surface planarity. A dense array of Cu features is typically formed in an interlayer dielectric, such as a silicon oxide layer, by a damascene technique wherein trenches are initially formed. A barrier layer, such as a Ta-containing layer e.g., Ta, TaN, is then deposited lining the trenches and on the upper surface of the silicon oxide interlayer dielectric. Cu or a Cu alloy is then deposited, as by electroplating, electroless plating, physical vapor deposition (PVD) at a temperature of about 50°C to about 150°C or chemical vapor deposition (CVD) at a temperature under about 200°C, typically at a thickness of about 8,000Å to about 18,000Å. CMP is then conducted to remove the Cu or Cu alloy overburden stopping on the barrier layer. Buffing is then conducted to remove the barrier layer, employing a mixture of a chemical agent and abrasive particles, leaving a Cu or the Cu alloy filling the damascene opening with an exposed surface. Overpolishing, as at about 10% to about 25%, is typically conducted beyond the time required to reach the interlayer dielectric, as determined by conventional end point detection techniques, e.g., to completely remove the barrier layer. For example, if 300 seconds of polishing are required to reach the targeted surface, 20% overpolishing would involve a total polishing time of 360 seconds. Conventional CMP techniques employing polishing pads utilizing slurries containing abrasive particles as well as CMP techniques employing fixed abrasive articles are characterized by excessive dishing sensitivity to overpolishing.

Dishing occurs wherein a portion of the surface of the inlaid metal of the interconnection formed in the groove in the interlayer dielectric is excessively polished resulting in one or more concavities or depressions. For example, adverting to Fig. 1, conductive lines 11 and 12 are formed by depositing a metal, such as Cu or a Cu alloy, in a damascene opening formed in interlayer dielectric 10, e.g., silicon dioxide. Subsequent to planarization, a portion of the inlaid metal 12 is depressed by an amount D referred to as the amount of dishing. For example, dishing occurring in metal lines, such as Cu or Cu alloy metal lines having a width of about 50 microns, generally exceeds 1,000Å with as little overpolish as about 5% to about 10%.

Another phenomenon resulting from conventional planarization techniques is known as erosion which is characterized by excessive polishing of the layer not targeted for

removal. For example, referring to Fig. 2, metal line 21 and dense array of metal lines 22 are inlaid in interlayer dielectric 20. Subsequent to planarization, excessive polishing of the interlayer material results in erosion E.

Dishing disadvantageously results in a non-planar via that impairs the ability to print high resolution lines during subsequent photolithographic steps. Dishing can also cause the formation of shorts or open circuits in the metal interconnection formed thereover. Moreover, dishing increases with longer overpolishing than when overpolishing is conducted to ensure complete removal of the metal layer and/or barrier layer across the wafer surface.

Conventional CMP techniques employ abrasives, such as an abrasive-containing slurry for use on a conventional polishing pad. The use of abrasives disadvantageously results in a high degree of dishing and erosion, because of pressure transmitted through the abrasive particle to the metal. In addition, the use of abrasives significantly increases the cost of consumables, as abrasives and suspension agents, as well as post CMP effluent treatment, are expensive.

There exists a need for CMP methodology enabling the planarization of inlaid metal, particularly inlaid Cu metallization, with reduced dishing and insensitivity to overpolishing.

Disclosure of the Invention

An aspect of the present invention is an efficient method of planarizing inlaid metals, such as Cu and Cu alloys, with significantly reduced dishing and significantly reduced sensitivity to overpolishing.

According to the present invention, the foregoing and other aspects are achieved in part by a method of removing at least part of a material, e.g., metal, from a substrate surface, the method comprising CMP the substrate surface using a composition having a pH and oxidation-reduction potential in the domain of passivation of the material.

Another aspect of the present invention is a method of manufacturing a semiconductor device, the method comprising planarizing a deposited Cu or Cu alloy layer on a dielectric layer by CMP employing a composition comprising: one or more chelating agents; one or more oxidizers, one or more corrosion inhibitors; one or more pH adjusting agents; and deionized water.

Embodiments of the present invention comprise CMP inlaid Cu metallization employing an abrasive-free polishing composition having a pH and oxidation-reduction

potential in the domain of passivation of Cu and having a low static etching rate with respect to Cu. Embodiments of the present invention include polishing compositions comprising one or more chelating agents, such as ethylenediaminetetraacetic acid, ethylenediamine or methylformamide, one or more oxidizers, such as hydrogen peroxide, 5 ferric nitrate or an iodate, one or more corrosion inhibitors, such as benzotriazole, mercaptobenzotriazole or 5-methyl-1-benzotriazole, one or more acids or bases sufficient to achieve a pH of about 3 to about 10, such as a pH of about 5 to about 8, e.g., an inorganic and/or organic acid, the remainder deionized water.

Additional aspects of the present invention will become readily apparent to those 10 skilled in this art from the following detailed description, wherein embodiments of the present invention are described, simply by way of illustration of the best mode contemplated for carrying out the present invention. As will be realized, the present invention is capable of other and different embodiments, and its several details are capable of modifications in various obvious respects, all without departing from the present 15 invention. Accordingly, the drawings and description are to be regarded as illustrative in nature, and not as restrictive.

Brief Description of Drawings

Fig. 1 schematically illustrates the phenomenon of dishing.

Fig. 2 schematically illustrates the phenomenon of erosion.

20 Fig. 3 is a pH-oxidation/reduction potential diagram for copper.

Figs. 4-6 schematically illustrate sequential phases of a method in accordance with an embodiment of the present invention.

Description of the Invention

The present invention enables effective and efficient planarization of inlaid metal, 25 e.g., Cu metallization, with significantly reduced dishing, erosion and overpolish sensitivity, thereby avoiding the disadvantages attendant upon forming a non-planar surface, such as a non-planar via. Such disadvantages include the impairment of the ability to print high resolution lines during photolithographic processing, and the formation of voids or open circuits in the interconnection formed thereover. Additional disadvantages attendant upon 30 conventional CMP stem from the use of abrasives, either abrasive-containing slurries or fixed abrasive articles, which significantly increase dishing and erosion, and significantly

increase the cost of CMP methodology. As used throughout this disclosure, the symbol Cu is intended to encompass high purity elemental copper as well copper-based alloys, e.g., copper-based alloys containing at least about 80 wt.% copper.

Aspects of the present invention are implemented by providing CMP methodology
5 employing a polishing composition formulated to passivate metal films. Such polishing compositions exhibit a greatly reduced static etching rate, i.e., etching rate in the absence of mechanical abrasion, even at elevated temperatures, thereby reducing dishing and erosion.

Conventional CMP methodology employs polishing compositions require strong
mechanic abrasive action which leads to excessive dishing and erosion. The present
10 invention overcomes problems attendant upon high dishing, erosion and overpolishing sensitivity by providing CMP methodology employing polishing compositions which form a passivation film over the metal surface, e.g., Cu, thereby reducing the static etching rate. For example, conventional CMP methodology employing abrasive slurries exhibit a Cu static etching rate greater than 300Å per minute at 52°C and greater than 730Å per minute at
15 52°C for fixed abrasive copper CMP. Dishing in 50 micron conductive lines exceeds 1,000Å with very little overpolish, e.g., about 5% to about 10%, due to abrasive particles.

In an embodiment of the present invention, CMP is conducted without an abrasive, as by employing an abrasive-free polishing composition with a conventional polishing pad, thereby significantly reducing dishing and erosion, and significantly reducing the cost of
20 conducting CMP. Embodiments of the present invention also include CMP using the polishing compositions containing abrasive particles or with fixed abrasive articles. Polishing compositions suitable for use in practicing embodiments of the present invention include those disclosed in copending application Serial No. _____ filed on _____ (Our Docket No. 49959-101). Such polishing compositions comprise
25 one or more chelating agents, such as a chelating agent containing one or more amine or amide groups, e.g., ethylenediaminetetraacetic, ethylenediamine or methylformamide. The chelating agent can be present in a suitable amount, such as about 0.2 wt.% to about 3.0 wt.%. The compositions in accordance with the present invention further comprise one or more oxidizers, one or more corrosion inhibitors, one or more pH adjusting agents and
30 deionized water. The oxidizer or oxidizers can be any of various conventional oxidizers employed in CMP, such as hydrogen peroxide, ferric nitrate or an iodate, and can be present in a suitable amount, such as about 0.5 wt.% to about 8.0 wt.%. The corrosion inhibitor or inhibitors can comprise any various organic compounds containing an azole group, such as

benzotriazole, mercaptobenzotriazole, or 5-methyl-1-benzotriazole, and can be present in a suitable amount, such as about 0.02 wt.% to about 1.0 wt.%. The pH adjusting agent or agents can be present in an amount for adjusting the pH of the composition to a range of about 3 to about 10 and can comprise any of various bases or inorganic and/or organic acids, such as acetic acid, phosphoric acid, or oxalic acid. Conventional abrasive particles
5 can be incorporated in the polishing composition, e.g., in an amount up to about 10% wt.%, such as up to about 1.0 wt.%, e.g., up to about 0.1 wt.%.

Some embodiments of the present invention comprise CMP of Cu, with or without polishing a barrier layer. In CMP of Cu, it was found suitable to formulate the polishing
10 composition such that it has a pH and oxidation-reduction potential in the domain of passivation of Cu.

Conventional substrates and interlayer dielectrics are encompassed by the present invention. For example, the substrate can be doped monocrystalline silicon or gallium-arsenide. The interlayer dielectric can comprise any of various dielectric materials
15 conventionally employed in the manufacture of semiconductor devices. For example, dielectric materials, such as silicon dioxide, phosphorous-doped silicon-glass (PSG), boron-phosphorous-doped silicon glass (BPSG) and silicon dioxide derived from tetraethyl orthosilicate (TEOS) or silane by plasma enhanced chemical vapor deposition (PECVD) can be employed. Interlayer dielectrics in accordance with the present invention can also
20 comprise low dielectric constant materials, including polymers, such as polyamides, and carbon-containing silicon dioxide, e.g., Black Diamond dielectric available from Applied Materials, Inc., located in Santa Clara, California. The openings are formed in interlayer dielectrics by conventional photolithographic and etching techniques.

Advantageously, abrasive-free CMP methodology in accordance with an
25 embodiment of the present invention can be employed with various commercial polishing pads. Optimum process parameters for CMP can be easily determined in a particular situation. For example, methodology in accordance with the abrasive-free CMP embodiment employs a polishing pressure of about 1 to about 8 psi, and a platen speed of about 20 to 120 rpm for a polishing duration of about 30 seconds to 2,000 seconds.
30 Advantageously, the abrasive-free CMP embodiment can be employed to planarize any of various films such as metal films, e.g., tungsten, aluminum, titanium, titanium nitride and nickel.

An embodiment of the present invention is schematically illustrated in Figs. 4-6, wherein similar features bear similar reference numerals. Adverting to Fig. 4, interlayer dielectric 40, e.g., silicon oxide, is formed overlying a substrate (not shown). A plurality of openings 41 are formed in a designated area A in which a dense array of conductive lines are to be formed bordering an open field B. A barrier layer 42, e.g., TaN, is deposited lining the openings 41 and on the upper surface of silicon oxide interlayer dielectric 40. Typically, the openings 41 are spaced apart by a distance C which is less than about 1 micron, e.g., about 0.2 micron. Cu layer 43 is then deposited at a thickness D of about 8,000Å to about 18,000Å.

Adverting to Fig. 5, CMP is conducted employing an abrasive-free, noble polishing composition to remove the Cu overburden stopping on TaN barrier layer 42, employing a conventional end point detection technique, with significantly reduced dishing. As shown in Fig. 6, buffing is conducted and overpolishing, with reduced dishing. Alternatively CMP can be conducted in one stage to remove the Cu overburden with overpolishing, using the abrasive-free noble polishing composition, with reduced dishing and reduced sensitivity to overpolishing. The resulting Cu interconnection structure comprises a dense array A of Cu lines 43 bordered by open field B. However, the upper surface 60 of the Cu metallization exhibits significantly reduced dishing.

The present invention is applicable to planarizing a wafer surface during various stages of semiconductor manufacturing by any of various CMP techniques using any of various CMP systems and polishing articles, e.g., fixed abrasive- or abrasive slurry-type pads or sheets. The present invention enjoys particular applicability in the manufacture of high density semiconductor devices with metal features in the deep submicron range.

Only the preferred embodiment of the present invention and but a few examples of its versatility are shown and described in the present disclosure. It is to be understood that the present invention is capable of use in various other combinations and environments and is capable of changes and modifications within the scope of the inventive concept as expressed herein.

What is Claimed Is:

1. A method of removing at least a part of a material from a substrate surface, the method comprising chemical-mechanical polishing (CMP) the substrate using a composition having a pH and oxidation-reduction potential in the domain of passivation of the material.
2. The method according to claim 1, wherein the material is a metal.
3. The method according to claim 2, wherein the metal comprises copper (Cu) or a Cu alloy.
4. The method according to claim 3, wherein the composition comprises:
one or more chelating agents;
one or more oxidizers;
one or more corrosion inhibitors;
optionally one or more agents to adjust the pH; and
deionized water.
5. The method according to claim 4, wherein the composition has a static etching rate of no greater than about 200Å per minute at about 52°C.
6. The method according to claim 5, wherein the composition has a pH of about 3.0 to about 10.0.
7. The method according to claim 4, comprising CMP the substrate with an abrasive-free slurry without employing any abrasive.
8. The method according to claim 4, wherein the composition contains up to 10 wt.% of abrasive particles.
9. The method according to claim 8, wherein the composition contains up to 1 wt.% of abrasive particles.
10. The method according to claim 9, wherein the composition contains up to 0.1 wt.% abrasive particles.

11. A method of manufacturing a semiconductor device, the method comprising planarizing a deposited Cu or Cu alloy layer on a dielectric layer by the CMP method according to claim 6.

12. The method according to claim 11, comprising:

forming an interlayer dielectric having at least one opening therein over the substrate;

5 depositing a barrier layer and Cu or a Cu alloy to fill the opening and form a layer on the interlayer dielectric; and

CMP to remove the Cu or Cu alloy layer from the interlayer dielectric to form a planarized surface.

13. The method according to claim 12, wherein the amount of dishing is less than about 600Å and the erosion is less than about 50Å at about 58% overpolishing.

14. The method according to claim 2, wherein the metal comprises aluminum, tungsten, titanium, titanium nitride or nickel.

15. The method according to claim 3, comprising conducting CMP at a pressure of about 1 to about 8 psi and a platen speed of about 20 to about 120 rpm for about 30 seconds to about 2,000 seconds.

16. A method of removing at least a part of a material from a substrate surface, the method comprising chemical-mechanical polishing (CMP) the substrate using a composition having a pH and oxidation-reduction potential in the domain of passivation of the material, wherein the composition comprises:

5 one or more chelating agents;
one or more oxidizers;
one or more corrosion inhibitors;
optionally one or more agents to adjust the pH; and
deionized water.

17. The method according to claim 16, wherein the composition has a static etching rate of no greater than about 200Å per minute at about 52°C.

18. The method according to claim 16, wherein the composition has a pH of about 3.0 to about 10.0.

19. The method according to claim 16, wherein the composition contains up to 10 wt.% of abrasive particles.

20. A method of removing at least a part of a material from a substrate surface, the method comprising chemical-mechanical polishing (CMP) the substrate using a composition having a pH and oxidation-reduction potential in the domain of passivation of the material, comprising:

5 forming an interlayer dielectric having at least one opening therein over the substrate;

depositing a barrier layer and Cu or a Cu alloy to fill the opening and form a layer on the interlayer dielectric; and

10 CMP to remove the Cu or Cu alloy layer from the interlayer dielectric to form a planarized surface.

21. The method of claim 20, wherein the composition contains up to 0.1 wt.% abrasive particles.

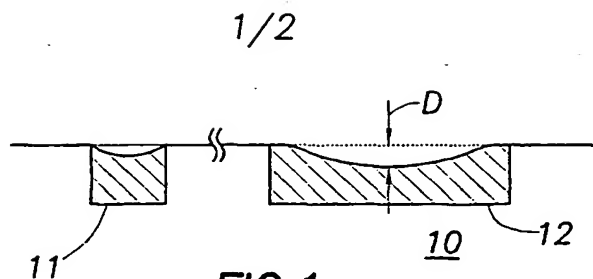


FIG. 1

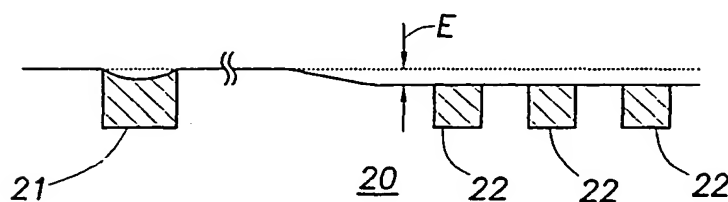


FIG. 2

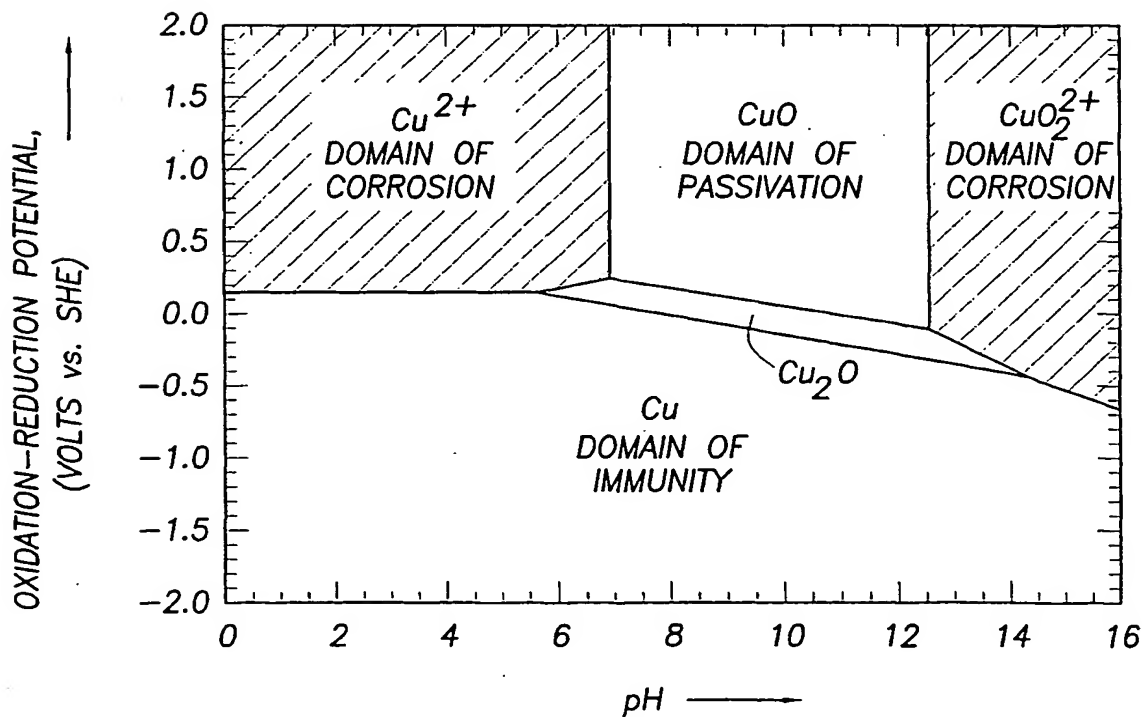


FIG. 3

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FIG. 4

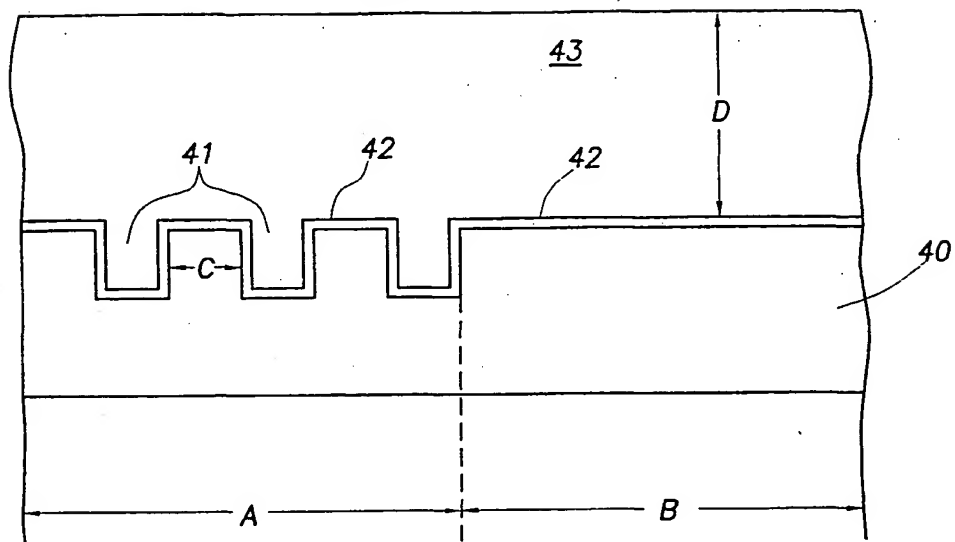


FIG. 5

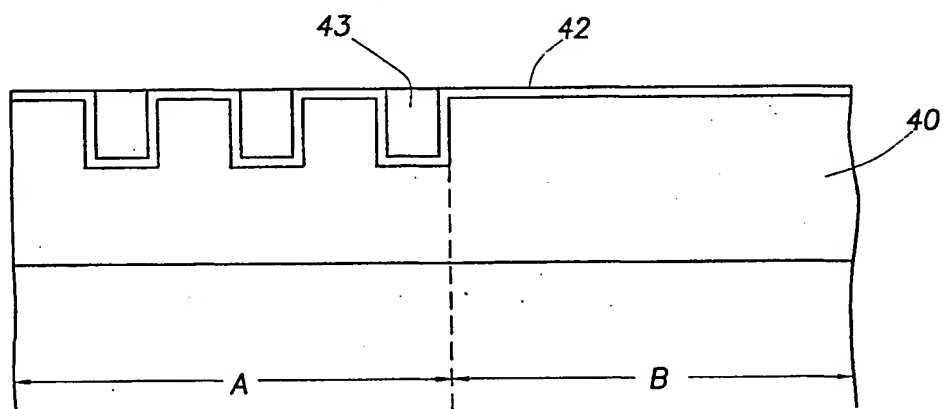
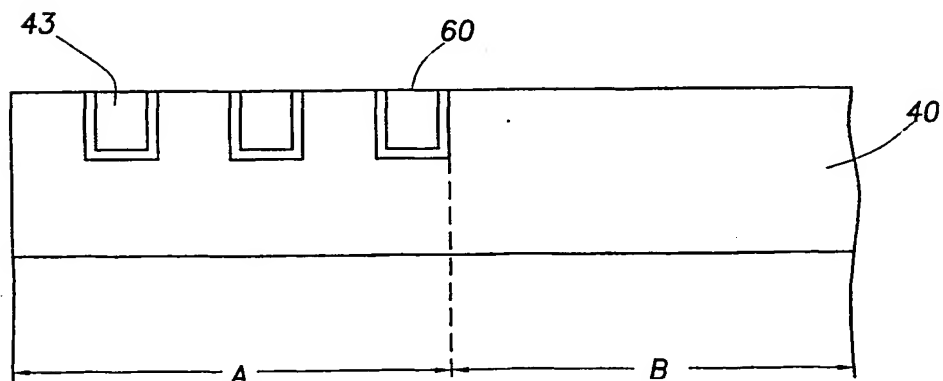


FIG. 6



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United States of America

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Assistant Secretary

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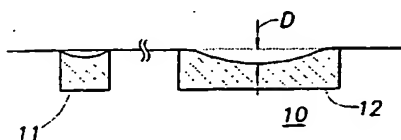
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(54) Title: **ABRASIVE-FREE METAL CMP IN PASSIVATION DOMAIN**



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(57) Abstract: Metal CMP with reduced dishing and overpolish insensitivity is achieved with an abrasive-free polishing composition having a pH and oxidation-reduction potential in the domain of passivation of the metal and, therefore, a low static etching rate at high temperatures, e.g., higher than 50°. Embodiments of the present invention comprise CMP of Cu film without any abrasive using a composition comprising one or more chelating agents, one or more oxidizers, one

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Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal, WPI Data, PAJ

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	WO 98 49723 A (WOOD THOMAS E ;HARDY L CHARLES (US); KAISAKI DAVID A (US); KRANZ H) 5 November 1998 (1998-11-05) the whole document	1-12, 15-21
X A	EP 0 659 858 A (TOKYO SHIBAURA ELECTRIC CO) 28 June 1995 (1995-06-28) the whole document	1-3, 15, 20, 21 4-12, 16-19
X	US 5 985 748 A (MENDONCA JOHN ET AL) 16 November 1999 (1999-11-16) the whole document	1-4, 7-12, 14-16, 18-21

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Date of the actual completion of the international search

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C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

Category	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US 5 770 095 A (HIGUCHI MASATOSHI ET AL) 23 June 1998 (1998-06-23) the whole document ---	1-6, 8, 11-13, 15-20
X	EP 0 846 742 A (CABOT CORP) 10 June 1998 (1998-06-10) the whole document ---	1-4, 8, 9, 11, 12, 14, 16, 18-20
X	WO 00 00561 A (CABOT CORP) 6 January 2000 (2000-01-06) the whole document ---	1-4, 8, 9, 11, 12, 16, 18-20
X	US 5 840 629 A (CARPIO RONALD A) 24 November 1998 (1998-11-24) the whole document ---	1-3
X	US 5 866 031 A (KALPATHY-CRAMER JAYASHREE ET AL) 2 February 1999 (1999-02-02) the whole document -----	1, 2, 14

INTERNATIONAL SEARCH REPORT

Information on patent family members

International Application No

PCT/US 01/11374

Patent document cited in search report		Publication date	Patent family member(s)	Publication date
WO 9849723	A	05-11-1998	AU 734883 B2 AU 7170698 A BR 9809311 A CN 1254441 T EP 1016133 A1 WO 9849723 A1	21-06-2001 24-11-1998 04-07-2000 24-05-2000 05-07-2000 05-11-1998
EP 0659858	A	28-06-1995	DE 69425812 D1 DE 69425812 T2 EP 0659858 A2 JP 7233485 A KR 165145 B1 US 5575885 A	12-10-2000 08-02-2001 28-06-1995 05-09-1995 15-01-1999 19-11-1996
US 5985748	A	16-11-1999	NONE	
US 5770095	A	23-06-1998	JP 8083780 A KR 188365 B1	26-03-1996 01-06-1999
EP 0846742	A	10-06-1998	US 5954997 A US 6126853 A AU 5373998 A EP 0846742 A2 JP 11021546 A TW 419714 B WO 9826025 A1	21-09-1999 03-10-2000 03-07-1998 10-06-1998 26-01-1999 21-01-2001 18-06-1998
WO 0000561	A	06-01-2000	US 6217416 B1 AU 4723499 A CN 1312843 T EP 1090083 A1 WO 0000561 A1	17-04-2001 17-01-2000 12-09-2001 11-04-2001 06-01-2000
US 5840629	A	24-11-1998	NONE	
US 5866031	A	02-02-1999	NONE	